

10/050 273

Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. M22-1896	SERIAL NO. 09/633,556
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT Gurtej S. Sandhu et al.	
				FILING DATE August 7, 2000	GROUP 2813

U.S. PATENT DOCUMENTS							
*Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
[Handwritten initials]	AA	5,032,545	07/91	Doan et al.			
	AB	5,436,481	07/93	Egawa et al.			
	AC	5,378,645	01/93	Inoue et al.			
	AD	5,258,333	11/93	Shappir et al.			
	AE	5,518,946	05/96	Kuroda			
	AF	5,445,999	08/95	Thakur et al.			
	AG	5,382,533	01/95	Ahmad et al.			
	AH	5,663,077	09/97	Adachi et al.			
	AI	5,026,574	06/91	Economu et al.			
	AJ	5,026,574	06/91	Economu et al.			
	AK	5,612,558	3/1997	Harshfield			
	AL	5,719,083	2/1998	Komatsu			

FOREIGN PATENT DOCUMENTS							
Document Number	Date	Country	Class	Subclass	Translation		
					Yes	No	
AM	WO 96/39713	12/96	PCT				
AN							
AO							
AP							
AQ							

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)		
[Handwritten initials]	AR	Wolf, S., "Silicon Processing for the VLSI Era", Lattice Press 1990, Vol. 2, pp. 212-213.
[Handwritten initials]	AS	Wolf, S., "Silicon Processing for the VLSI Era", Lattice Press 1990, Vol. 2, pp. 188-189, 194-195, 609-614.
	AT	Ko, L. et al., "The Effect of Nitrogen Incorporation into the Gate Oxide By Using Shallow Implantation of Nitrogen and Drive-In Process", IEEE 1996, pp. 32-35.

EXAMINER [Handwritten signature]	DATE CONSIDERED 9/30/02
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Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. M122-1896	SERIAL NO. 10/050373 09/833,556			
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT Gurtej S. Sandhu et al.				
				FILING DATE August 7, 2000	GROUP 2813			
U.S. PATENT DOCUMENTS								
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
<i>[initials]</i>	AA	5,760,475	06/98	Croain				
<i>[initials]</i>	AB	5,834,372	11/98	Lee				
<i>[initials]</i>	AC	5,619,057	04/99	Komatsu				
<i>[initials]</i>	AD	5,633,036	05/97	Seebauer et al.				
<i>[initials]</i>	AE	6,054,396	04/00	Doan				
<i>[initials]</i>	AF	6,174,821	01/01	Doan				
<i>[initials]</i>	AG	5,939,750	08/99	Early				
<i>[initials]</i>	AH	5,254,489	10/93	Nakata				
<i>[initials]</i>	AI	5,464,792	11/95	Tseng et al.				
<i>[initials]</i>	AJ	5,620,908	04/97	Inoh et al.				
<i>[initials]</i>	AK	5,716,864	02/98	Abe				
<i>[initials]</i>	AL	5,972,783	10/99	Arai et al.				
FOREIGN PATENT DOCUMENTS								
		Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
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	AR	Doyle, B. et al., "Simultaneous Growth of Different Thickness Gate Oxides in Silicon CMOS Processing", IEEE Vol. 16 (7), July 1995, pp. 301-302.						
	AS	Kuroi, T. et al., "The Effects of Nitrogen Implantation Into P+Poly-Silicon Gate on Gate Oxide Properties", 1994 Sympos. on VLSI Technology Digest of Technical Papers, IEEE 1994, pp. 107-108.						
	AT	Liu, C.T. et al., "Multiple Gate Oxide Thickness for 2GHz System-on-a-Chip Technologies", IEEE 1998, pp. 589-592.						
EXAMINER <i>[Signature]</i>				DATE CONSIDERED 9/30/02				
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LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT Gurtej S. Sandhu et al.				
				FILING DATE 11/5/02 August 7, 2000	GROUP 2813			
U.S. PATENT DOCUMENTS								
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
<i>WJS</i>	AA	6,091,109	07/00	Hasegawa				
<i>WJS</i>	AB	6,080,682	06/00	Ibok				
<i>WJS</i>	AC	5,685,949	11/97	Yashima				
<i>WJS</i>	AD	6,268,296 B1	07/01	Misium et al.				
<i>WJS</i>	AE	6,232,244 B1	05/01	Ibok				
	AF							
	AG							
	AH							
	AI							
	AJ							
	AK							
	AL							
FOREIGN PATENT DOCUMENTS								
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	AN							
	AO							
	AP							
	AQ							
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)								
	AR							
	AS							
	AT							
EXAMINER <i>Wesley Schultz</i>				DATE CONSIDERED <i>9/30/02</i>				
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